1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOT1289 (CFP15) power and flat lead Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- Average forward current: I_{F(AV)} ≤ 10 A
- Reverse voltage: V_R ≤ 45 V
- Extremely low forward voltage
- · High power capability due to clip-bonding technology and heat sink
- Small and thin SMD power plastic package, typical height 0.78 mm

3. Applications

- · Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Freewheeling application
- Reverse polarity protection
- Low power consumption application

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{F(AV)}	average forward current	δ = 0.5; f = 20 kHz; $T_{sp} \le$ 130 °C; square wave	-	-	10	А
V_R	reverse voltage	T _j = 25 °C	-	-	45	V
V _F	forward voltage	I_F = 10 A; $t_p \le 300 \mu s$; δ ≤ 0.02; T_j = 25 °C; pulsed	-	430	490	mV
I _R	reverse current	V_R = 10 V; t_p ≤ 3 ms; δ = 0.3; T_j = 25 °C; pulsed	-	20	50	μΑ
		$V_R = 45 \text{ V; } t_p \le 3 \text{ ms; } \delta = 0.3;$ $T_j = 25 \text{ °C; pulsed}$	-	230	600	μΑ





5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Α	anode		K PA
2	Α	anode	3	aaa-009063
3	K	cathode	2 CFP15 (SOT1289)	

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMEG45U10EPD	CFP15	plastic, thermal enhanced ultra thin SMD package; 3 leads; body: 5.8 x 4.3 x 0.78 mm	SOT1289

7. Marking

Table 4. Marking codes

Type number	Marking code
PMEG45U10EPD	4510 UUUU

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _R	reverse voltage	T _j = 25 °C		-	45	V
I _F	forward current	T _{sp} = 125 °C; δ = 1		-	14	Α
I _{F(AV)}	average forward current	δ = 0.5; f = 20 kHz; $T_{sp} \le$ 130 °C; square wave		-	10	A
I _{FSM}	non-repetitive peak forward current	t_p = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	180	A
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.9	W
			[2]	-	1.2	W
			[3]	-	3	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C

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Symbol	Parameter	Conditions	Min	Max	Unit
T _{stg}	storage temperature		-65	150	°C

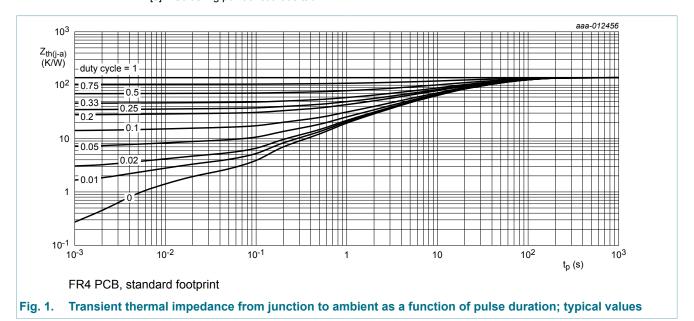
- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [3] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient		in free air	[1][2]	-	-	165	K/W
		[1][3]	-	-	120	K/W	
	ambient		[1][4]	-	-	50	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		[5]	-	-	4	K/W

- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [5] Soldering point of cathode tab.



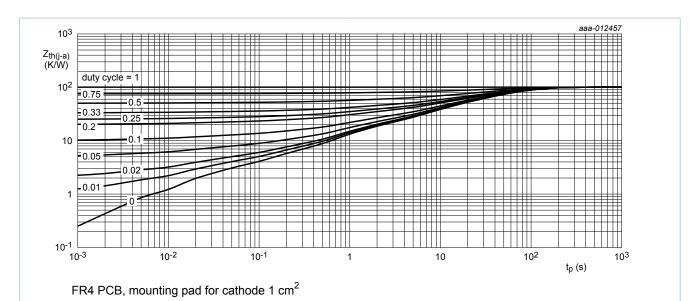


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

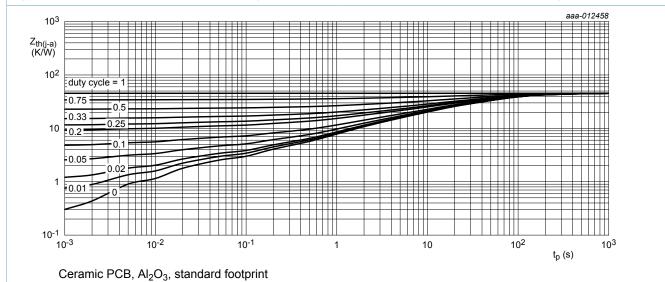
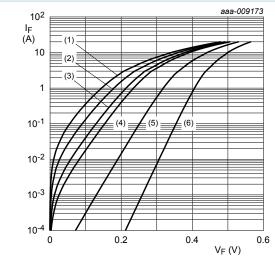


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _F	forward voltage	I_F = 1 A; $t_p \le 300 \ \mu s$; δ ≤ 0.02; T_j = 25 °C; pulsed	-	314	360	mV
		I_F = 2 A; $t_p \le 300 \text{ μs}$; $\delta \le 0.02$; T_j = 25 °C; pulsed	-	338	-	mV
		I_F = 3 A; t_p ≤ 300 μs; δ ≤ 0.02; T_j = 25 °C; pulsed	-	355	-	mV
		I_F = 5 A; t_p ≤ 300 μs; δ ≤ 0.02; T_j = 25 °C; pulsed	-	380	430	mV
		I_F = 10 A; $t_p \le 300$ μs; $δ \le 0.02$; T_j = 25 °C; pulsed	-	430	490	mV
reverse current		V_R = 5 V; $t_p \le 3$ ms; δ = 0.3; T_j = 25 °C; pulsed	-	15	-	μA
		$V_R = 10 \text{ V}; t_p \le 3 \text{ ms}; \delta = 0.3;$ $T_j = 25 ^{\circ}\text{C}; \text{ pulsed}$	-	20	50	μA
		$V_R = 30 \text{ V}; t_p \le 3 \text{ ms}; \delta = 0.3;$ $T_j = 25 ^{\circ}\text{C}; \text{ pulsed}$	-	65	-	μA
		$V_R = 45 \text{ V}; t_p \le 3 \text{ ms}; \delta = 0.3;$ $T_j = 25 \text{ °C}; \text{ pulsed}$	-	230	600	μA
		$V_R = 10 \text{ V}; t_p \le 3 \text{ ms}; \delta = 0.3;$ $T_j = 125 ^{\circ}\text{C}; \text{ pulsed}$	-	20	-	mA
C _d	diode capacitance	V _R = 1 V; f = 1 MHz; T _j = 25 °C	-	1170	-	pF
		V _R = 10 V; f = 1 MHz; T _j = 25 °C	-	390	-	pF
t _{rr}	reverse recovery time step recovery	$I_F = 0.5 \text{ A}; I_R = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ $T_j = 25 \text{ °C}$	-	34	-	ns
t _{rr}	reverse recovery time ramp recovery	$dI_F/dt = 200 \text{ A/}\mu\text{s}; T_j = 25 ^{\circ}\text{C}; I_F = 6 \text{ A};$ $V_R = 26 \text{ V}$	-	16	-	ns
$V_{(BR)R}$	reverse breakdown voltage	I_R = 5 mA; T_j = 25 °C; t_p ≤ 1.2 ms; δ = 0.12; pulsed	45	-	-	V
V_{FRM}	peak forward recovery voltage	$I_F = 0.5 \text{ A}; dI_F/dt = 20 \text{ A/}\mu\text{s}; T_j = 25 °\text{C}$	-	300	-	mV



(1)
$$T_i = 150 \, ^{\circ}C$$

(2)
$$T_i = 125 \, ^{\circ}C$$

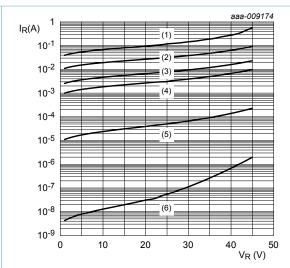
(3)
$$T_i = 100 \, ^{\circ}C$$

(4)
$$T_i = 85 \, ^{\circ}C$$

(5)
$$T_i = 25 \, ^{\circ}C$$

(6)
$$T_i = -40 \, ^{\circ}C$$

Fig. 4. Forward current as a function of forward voltage; typical values (pulsed condition)



(1)
$$T_i = 150 \, ^{\circ}C$$

(2)
$$T_j = 125 \,^{\circ}\text{C}$$

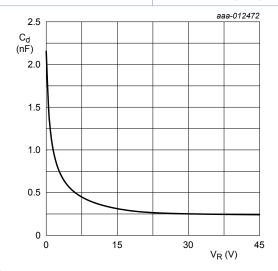
(3)
$$T_i = 100 \, ^{\circ}C$$

(4)
$$T_i = 85 \, ^{\circ}C$$

(5)
$$T_i = 25 \, ^{\circ}C$$

(6)
$$T_i = -40 \, ^{\circ}\text{C}$$

Fig. 5. Reverse current as a function of reverse voltage; typical values (pulsed condition)



 $f = 1 MHz; T_{amb} = 25 °C$

Fig. 6. Diode capacitance as a function of reverse voltage; typical values

11. Test information

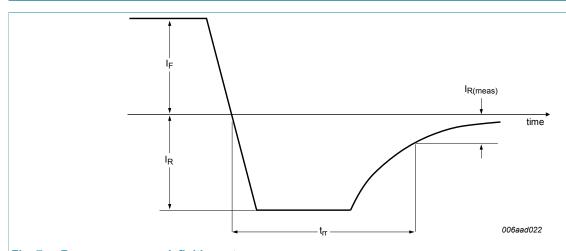


Fig. 7. Reverse recovery definition; step recovery

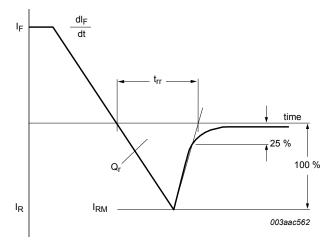


Fig. 8. Reverse recovery definition; ramp recovery

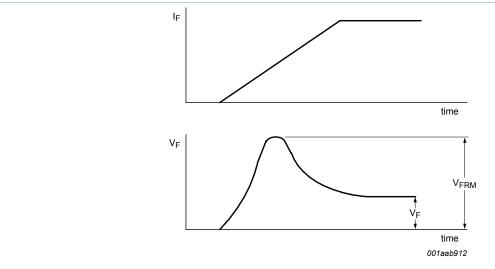
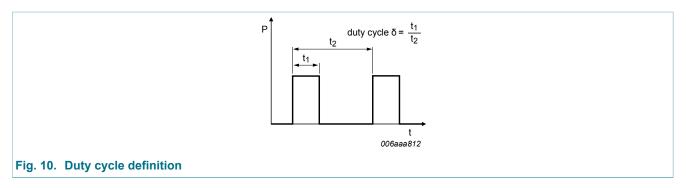


Fig. 9. Forward recovery definition

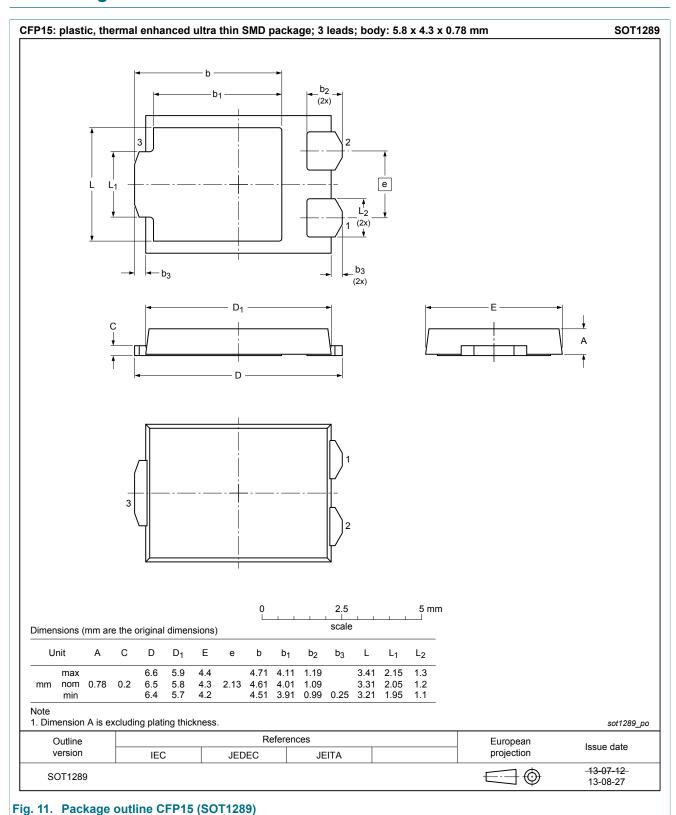
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The current ratings for the typical waveforms are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

8/14

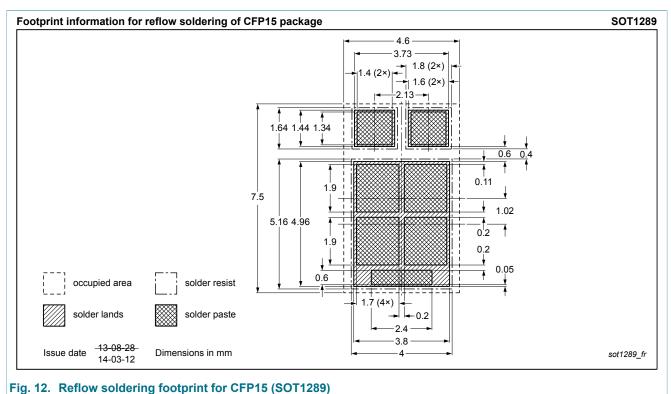
12. Package outline



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13. Soldering



14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PMEG45U10EPD v.2	20140416	Product data sheet	-	PMEG45U10EPD v.1		
Modifications:	Product status changed					
PMEG45U10EPD v.1	20140217	Objective data sheet	-	-		

11 / 14

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	2
9	Thermal characteristics	3
10	Characteristics	5
11	Test information	7
12	Package outline	9
13	Soldering	10
14	Revision history	11
15	Legal information	12
15.1	Data sheet status	12
15.2	Definitions	12
15.3	Disclaimers	12
15.4	Trademarks	13

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